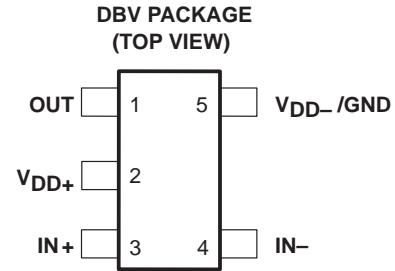


- **Output Swing Includes Both Supply Rails**
- **Low Noise . . . 15 nV/√Hz Typ at f = 1 kHz**
- **Low Input Bias Current . . . 1 pA Typ**
- **Fully Specified for Single-Supply 3-V and 5-V Operation**
- **Common-Mode Input Voltage Range Includes Negative Rail**
- **High Gain Bandwidth . . . 2 MHz at V_{DD} = 5 V with 600 Ω Load**
- **High Slew Rate . . . 1.6 V/μs at V_{DD} = 5 V**
- **Wide Supply Voltage Range 2.7 V to 10 V**
- **Macromodel Included**



description

The TLV2731 is a single low-voltage operational amplifier available in the SOT-23 package. It offers 2 MHz of bandwidth and 1.6 V/μs of slew rate for applications requiring good ac performance. The device exhibits rail-to-rail output performance for increased dynamic range in single or split supply applications. The TLV2731 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2731, exhibiting high input impedance and low noise, is excellent for small-signal conditioning of high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single- or split-supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). The device can also drive 600-Ω loads for telecom applications.

With a total area of 5.6mm², the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

AVAILABLE OPTIONS

T _A	V _{IO} max AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM‡ (Y)
		SOT-23 (DBV)†		
0°C to 70°C	3 mV	TLV2731CDBV	VALC	TLV2731Y
-40°C to 85°C	3 mV	TLV2731IDBV	VALI	

† The DBV package available in tape and reel only.

‡ Chip forms are tested at T_A = 25°C only.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Advanced LinCMOS is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



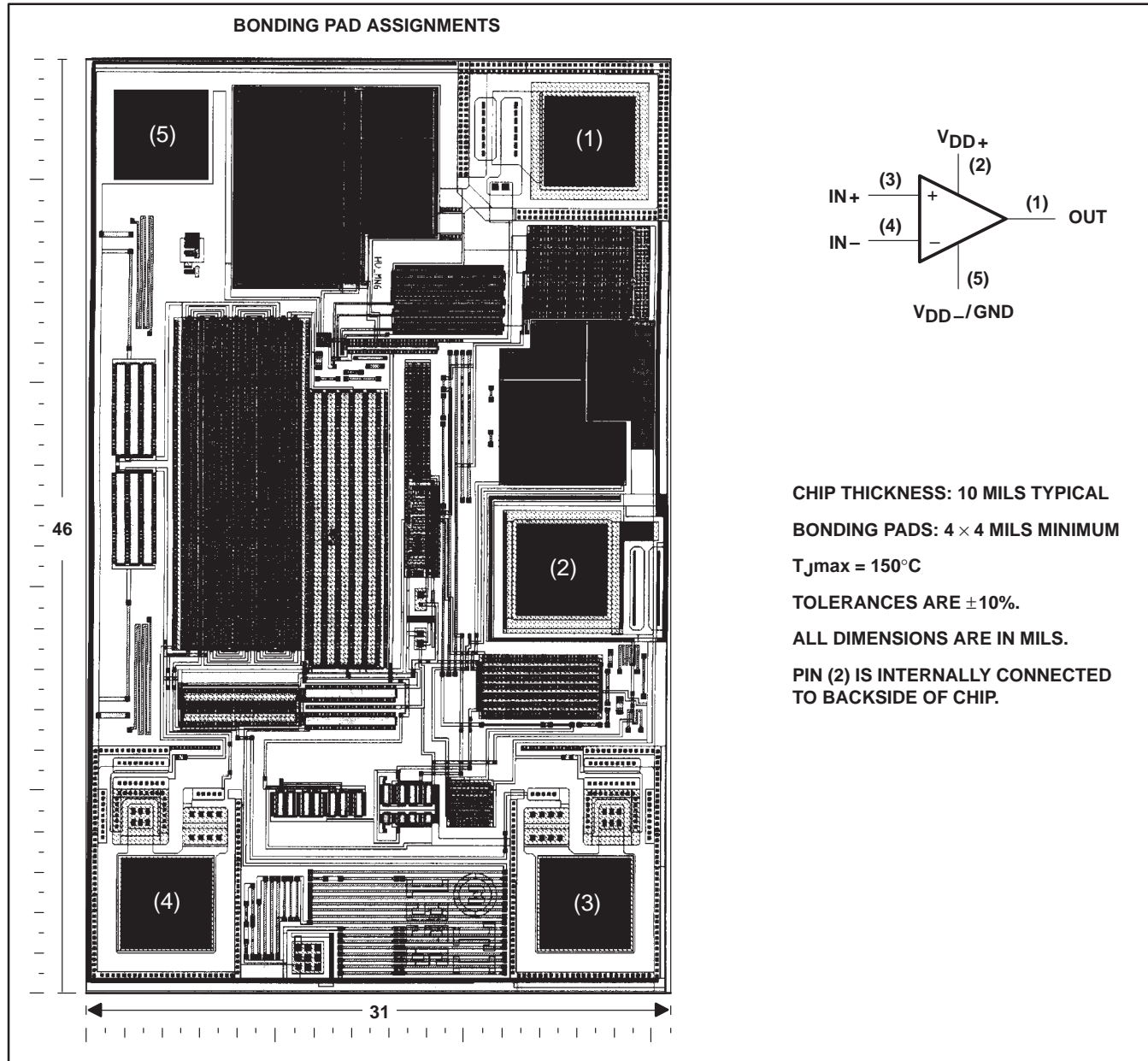
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1997, Texas Instruments Incorporated

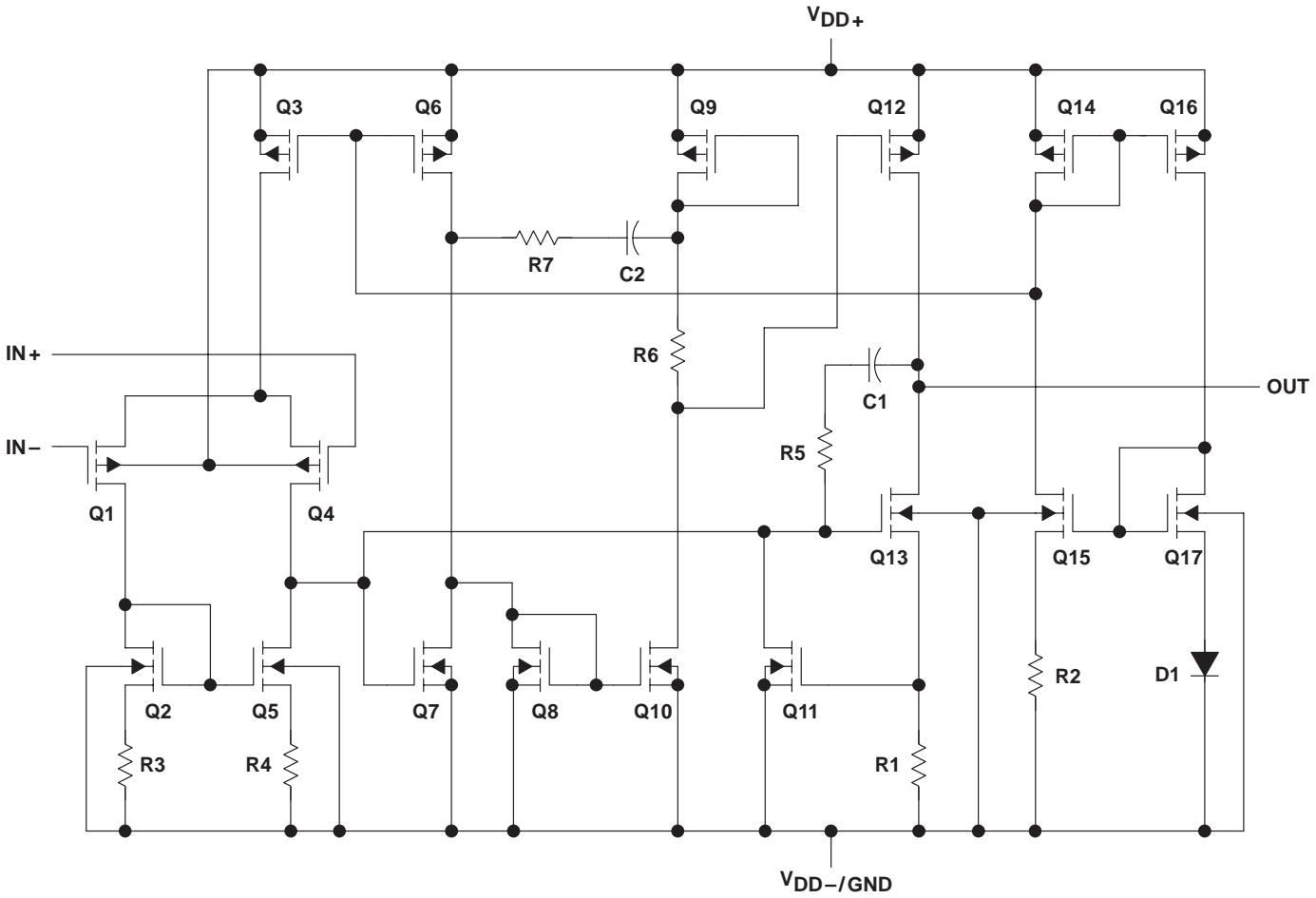
TLV2731, TLV2731Y
Advanced LinCMOS™ RAIL-TO-RAIL
LOW-POWER SINGLE OPERATIONAL AMPLIFIERS
 SLOS198 – AUGUST 1997

TLV2731Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2731C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.



equivalent schematic



COMPONENT COUNT†	
Transistors	23
Diodes	5
Resistors	11
Capacitors	2

† Includes both amplifiers and all ESD, bias, and trim circuitry

TLV2731, TLV2731Y
Advanced LinCMOS™ RAIL-TO-RAIL
LOW-POWER SINGLE OPERATIONAL AMPLIFIERS
 SLOS198 – AUGUST 1997

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1)	12 V
Differential input voltage, V_{ID} (see Note 2)	$\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1)	-0.3 V to V_{DD}
Input current, I_I (each input)	± 5 mA
Output current, I_O	± 50 mA
Total current into V_{DD+}	± 50 mA
Total current out of V_{DD-}	± 50 mA
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A : TLV2731C	0°C to 70°C
TLV2731I	-40°C to 85°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-} .
 2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below $V_{DD-} - 0.3$ V.
 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

recommended operating conditions

	TLV2731C		TLV2731I		UNIT
	MIN	MAX	MIN	MAX	
Supply voltage, V_{DD} (see Note 1)	2.7	10	2.7	10	V
Input voltage range, V_I	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Common-mode input voltage, V_{IC}	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Operating free-air temperature, T_A	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-} .



electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A †	TLV2731C			TLV2731I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD\pm} = \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	Full range	0.7 3			0.7 3			mV
α_{VIO} Temperature coefficient of input offset voltage			0.5			0.5			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5			0.5			pA
		Full range	150			150			
I_{IB} Input bias current		25°C	1			1			pA
	Full range	150			150				
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2	0 to 2	-0.3 to 2.2	V		
		Full range	0 to 1.7		0 to 1.7				
V_{OH} High-level output voltage	$I_{OH} = -1\text{ mA}$ $I_{OH} = -2\text{ mA}$	25°C	2.87			2.87			V
		25°C	2.74			2.74			
		Full range	2.3			2.3			
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$ $V_{IC} = 1.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C	10			10			mV
		25°C	100			100			
		Full range	300			300			
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$, $V_O = 1\text{ V to } 2\text{ V}$	25°C	$R_L = 600\ \Omega$ ‡			1 1.6			V/mV
			Full range			0.3			
		25°C	$R_L = 1\text{ M}\Omega$ ‡			250			
r_{id} Differential input resistance		25°C	10^{12}			10^{12}			Ω
r_{ic} Common-mode input resistance		25°C	10^{12}			10^{12}			Ω
c_{ic} Common-mode input capacitance	$f = 10\text{ kHz}$	25°C	6			6			pF
z_o Closed-loop output impedance	$f = 1\text{ MHz}$, $A_V = 1$	25°C	156			156			Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}$, $V_O = 1.5\text{ V}$, $R_S = 50\ \Omega$	25°C	60 70			60 70			dB
		Full range	55			55			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to } 8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	70 96			70 96			dB
		Full range	70			70			
I_{DD} Supply current	$V_O = 1.5\text{ V}$, No load	25°C	750 1200			750 1200			μA
		Full range	1500			1500			

† Full range for the TLV2731C is 0°C to 70°C. Full range for the TLV2731I is -40°C to 85°C.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2731, TLV2731Y
Advanced LinCMOS™ RAIL-TO-RAIL
LOW-POWER SINGLE OPERATIONAL AMPLIFIERS
 SLOS198 – AUGUST 1997

operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS	T_A †	TLV2731C			TLV2731I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain $V_O = 1.1\text{ V to }1.9\text{ V}, R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C	0.75	1.25		0.75	1.25		V/ μs
		Full range	0.5			0.5			
V_n	Equivalent input noise voltage $f = 10\text{ Hz}$ $f = 1\text{ kHz}$	25°C		105			105		nV/ $\sqrt{\text{Hz}}$
		25°C		16			16		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1\text{ Hz to }1\text{ Hz}$ $f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.4			1.4		μV
		25°C		1.5			1.5		
I_n	Equivalent input noise current	25°C		0.6			0.6		fA/ $\sqrt{\text{Hz}}$
THD+N	Total harmonic distortion plus noise $V_O = 1\text{ V to }2\text{ V}, f = 20\text{ kHz}, R_L = 600\ \Omega\ddagger$ $V_O = 1\text{ V to }2\text{ V}, f = 20\text{ kHz}, R_L = 600\ \Omega\§$	25°C		$A_V = 1$	0.285%		0.285%		
				$A_V = 10$	7.2%		7.2%		
		25°C		$A_V = 1$	0.014%		0.014%		
				$A_V = 10$	0.098%		0.098%		
				$A_V = 100$	0.13%		0.13%		
Gain-bandwidth product	$f = 10\text{ kHz}, C_L = 100\text{ pF}\ddagger, R_L = 600\ \Omega\ddagger$	25°C		1.9			1.9		MHz
BOM	Maximum output-swing bandwidth $V_{O(PP)} = 1\text{ V}, R_L = 600\ \Omega\ddagger, A_V = 1, C_L = 100\text{ pF}\ddagger$	25°C		60			60		kHz
t_s	Settling time $A_V = -1, \text{ Step} = 1\text{ V to }2\text{ V}, R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C		To 0.1%	0.9		0.9		μs
				To 0.01%	1.5		1.5		
ϕ_m	Phase margin at unity gain $R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C		50°			50°		
		25°C		8			8		dB

† Full range is -40°C to 85°C .

‡ Referenced to 1.5 V

§ Referenced to 0 V



electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A †	TLV2731C			TLV2731I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD\pm} = \pm 2.5\text{ V}$, $V_O = 0$, $V_{IC} = 0$, $R_S = 50\ \Omega$	Full range	0.7 3			0.7 3			mV
$\alpha_{V_{IO}}$ Temperature coefficient of input offset voltage			0.5			0.5			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5			0.5			pA
		Full range	150			150			
I_{IB} Input bias current		25°C	1			1			pA
	Full range	150			150				
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 4	-0.3 to 4.2	0 to 4	-0.3 to 4.2	V		
		Full range	0 to 3.7		0 to 3.7				
V_{OH} High-level output voltage	$I_{OH} = -1\text{ mA}$ $I_{OH} = -4\text{ mA}$	25°C	4.9			4.9			V
		25°C	4.6			4.6			
		Full range	4.3			4.3			
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$ $V_{IC} = 2.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C	80			80			mV
		25°C	160			160			
		Full range	500			500			
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$, $V_O = 1\text{ V to }4\text{ V}$	25°C	$R_L = 600\ \Omega$ ‡		1	1.5	1	1.5	V/mV
			Full range		0.3		0.3		
		25°C	$R_L = 1\text{ M}\Omega$ ‡		400		400		
r_{id} Differential input resistance		25°C	10^{12}			10^{12}			Ω
r_{ic} Common-mode input resistance		25°C	10^{12}			10^{12}			Ω
c_{ic} Common-mode input capacitance	$f = 10\text{ kHz}$	25°C	6			6			pF
z_o Closed-loop output impedance	$f = 1\text{ MHz}$, $A_V = 1$	25°C	138			138			Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }2.7\text{ V}$, $V_O = 2.5\text{ V}$, $R_S = 50\ \Omega$	25°C	60	70	60	70	dB		
		Full range	55			55			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	70	96	70	96	dB		
		Full range	70			70			
I_{DD} Supply current	$V_O = 2.5\text{ V}$, No load	25°C	850	1300	850	1300	μA		
		Full range	1600			1600			

† Full range for the TLV2731C is 0°C to 70°C. Full range for the TLV2731I is -40°C to 85°C.

‡ Referenced to 2.5 V

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2731, TLV2731Y
Advanced LinCMOS™ RAIL-TO-RAIL
LOW-POWER SINGLE OPERATIONAL AMPLIFIERS
 SLOS198 – AUGUST 1997

operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER	TEST CONDITIONS	T_A †	TLV2731C			TLV2731I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain $V_O = 1.5\text{ V to }3.5\text{ V}, R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C	1	1.6		1	1.6		V/ μs
		Full range	0.7			0.7			
V_n	Equivalent input noise voltage $f = 10\text{ Hz}$ $f = 1\text{ kHz}$	25°C		100			100		nV/ $\sqrt{\text{Hz}}$
		25°C		15			15		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1\text{ Hz to }1\text{ Hz}$ $f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.4			1.4		μV
		25°C		1.5			1.5		
I_n	Equivalent input noise current	25°C		0.6			0.6		fA/ $\sqrt{\text{Hz}}$
THD+N	Total harmonic distortion plus noise $V_O = 1.5\text{ V to }3.5\text{ V}, f = 20\text{ kHz}, R_L = 600\ \Omega\ddagger$	25°C	$A_V = 1$	0.409%			0.409%		
			$A_V = 10$	3.68%			3.68%		
	$V_O = 1.5\text{ V to }3.5\text{ V}, f = 20\text{ kHz}, R_L = 600\ \Omega\§$	25°C	$A_V = 1$	0.018%			0.018%		
			$A_V = 10$	0.045%			0.045%		
			$A_V = 100$	0.116%			0.116%		
Gain-bandwidth product	$f = 10\text{ kHz}, R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C		2			2	MHz	
B_{OM}	Maximum output-swing bandwidth $V_{O(PP)} = 1\text{ V}, R_L = 600\ \Omega\ddagger, A_V = 1, C_L = 100\text{ pF}\ddagger$	25°C		300			300	kHz	
t_s	Settling time $A_V = -1, \text{ Step} = 1.5\text{ V to }3.5\text{ V}, R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C	To 0.1%	0.95			0.95	μs	
			To 0.01%	2.4			2.4		
ϕ_m	Phase margin at unity gain $R_L = 600\ \Omega\ddagger, C_L = 100\text{ pF}\ddagger$	25°C		48°			48°		
		25°C		8			8	dB	

† Full range is -40°C to 85°C .

‡ Referenced to 2.5 V

§ Referenced to 0 V

electrical characteristics at $V_{DD} = 3\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TLV2731Y			UNIT
		MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $R_S = 50\ \Omega$	$V_{IC} = 0$,	$V_O = 0$,	750	μV
I_{IO} Input offset current				0.5	pA
I_{IB} Input bias current				1	pA
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$			-0.3 to 2.2	V
V_{OH} High-level output voltage	$I_{OH} = -1\text{ mA}$			2.87	V
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$,	$I_{OL} = 50\ \mu\text{A}$		10	mV
	$V_{IC} = 1.5\text{ V}$,	$I_{OL} = 500\ \mu\text{A}$		100	
A_{VD} Large-signal differential voltage amplification	$V_O = 1\text{ V to }2\text{ V}$	$R_L = 600\ \Omega^\dagger$		1.6	V/mV
		$R_L = 1\text{ M}\Omega^\dagger$		250	
r_{id} Differential input resistance				10^{12}	Ω
r_{ic} Common-mode input resistance				10^{12}	Ω
C_{ic} Common-mode input capacitance	$f = 10\text{ kHz}$			6	pF
Z_o Closed-loop output impedance	$f = 1\text{ MHz}$,	$A_V = 1$		156	Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }1.7\text{ V}$,	$V_O = 0$,	$R_S = 50\ \Omega$	70	dB
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to }8\text{ V}$,	$V_{IC} = 0$,	No load	96	dB
I_{DD} Supply current	$V_O = 0$,	No load		750	μA

† Referenced to 1.5 V

electrical characteristics at $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TLV2731Y			UNIT
		MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $R_S = 50\ \Omega$	$V_{IC} = 0$,	$V_O = 0$,	710	μV
I_{IO} Input offset current				0.5	pA
I_{IB} Input bias current				1	pA
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$			-0.3 to 4.2	V
V_{OH} High-level output voltage	$I_{OH} = -1\text{ mA}$			4.9	V
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$,	$I_{OL} = 500\ \mu\text{A}$		80	mV
	$V_{IC} = 2.5\text{ V}$,	$I_{OL} = 1\text{ mA}$		160	
A_{VD} Large-signal differential voltage amplification	$V_O = 1\text{ V to }2\text{ V}$	$R_L = 600\ \Omega^\dagger$		15	V/mV
		$R_L = 1\text{ M}\Omega^\dagger$		400	
r_{id} Differential input resistance				10^{12}	Ω
r_{ic} Common-mode input resistance				10^{12}	Ω
C_{ic} Common-mode input capacitance	$f = 10\text{ kHz}$			6	pF
Z_o Closed-loop output impedance	$f = 1\text{ MHz}$,	$A_V = 1$		138	Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }1.7\text{ V}$,	$V_O = 0$,	$R_S = 50\ \Omega$	70	dB
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to }8\text{ V}$,	$V_{IC} = 0$,	No load	96	dB
I_{DD} Supply current	$V_O = 0$,	No load		850	μA

† Referenced to 2.5 V

TYPICAL CHARACTERISTICS

Table of Graphs

		FIGURE
V_{IO}	Input offset voltage	Distribution vs Common-mode input voltage 2, 3 4, 5
α_{VIO}	Input offset voltage temperature coefficient	Distribution 6, 7
I_{IB}/I_{IO}	Input bias and input offset currents	vs Free-air temperature 8
V_I	Input voltage	vs Supply voltage vs Free-air temperature 9 10
V_{OH}	High-level output voltage	vs High-level output current 11, 14
V_{OL}	Low-level output voltage	vs Low-level output current 12, 13, 15
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency 16
I_{OS}	Short-circuit output current	vs Supply voltage vs Free-air temperature 17 18
V_O	Output voltage	vs Differential input voltage 19, 20
A_{VD}	Differential voltage amplification	vs Load resistance 21
A_{VD}	Large-signal differential voltage amplification	vs Frequency vs Free-air temperature 22, 23 24, 25
z_o	Output impedance	vs Frequency 26, 27
$CMRR$	Common-mode rejection ratio	vs Frequency vs Free-air temperature 28 29
k_{SVR}	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature 30, 31 32
I_{DD}	Supply current	vs Supply voltage 33
SR	Slew rate	vs Load capacitance vs Free-air temperature 34 35
V_O	Inverting large-signal pulse response	vs Time 36, 37
V_O	Voltage-follower large-signal pulse response	vs Time 38, 39
V_O	Inverting small-signal pulse response	vs Time 40, 41
V_O	Voltage-follower small-signal pulse response	vs Time 42, 43
V_n	Equivalent input noise voltage	vs Frequency 44, 45
	Noise voltage (referred to input)	Over a 10-second period 46
$THD + N$	Total harmonic distortion plus noise	vs Frequency 47
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage 48 49
	Gain margin	vs Load capacitance 50, 51
ϕ_m	Phase margin	vs Frequency vs Load capacitance 22, 23 52, 53
B_1	Unity-gain bandwidth	vs Load capacitance 54, 55

TYPICAL CHARACTERISTICS

**DISTRIBUTION OF TLV2731
INPUT OFFSET VOLTAGE**

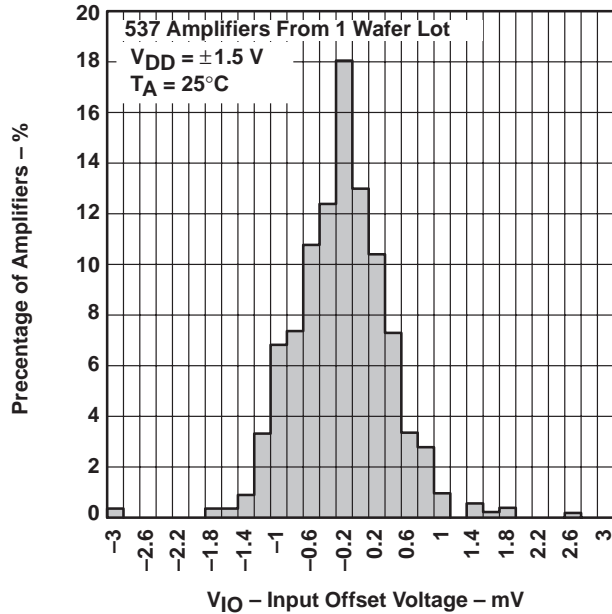


Figure 1

**DISTRIBUTION OF TLV2731
INPUT OFFSET VOLTAGE**

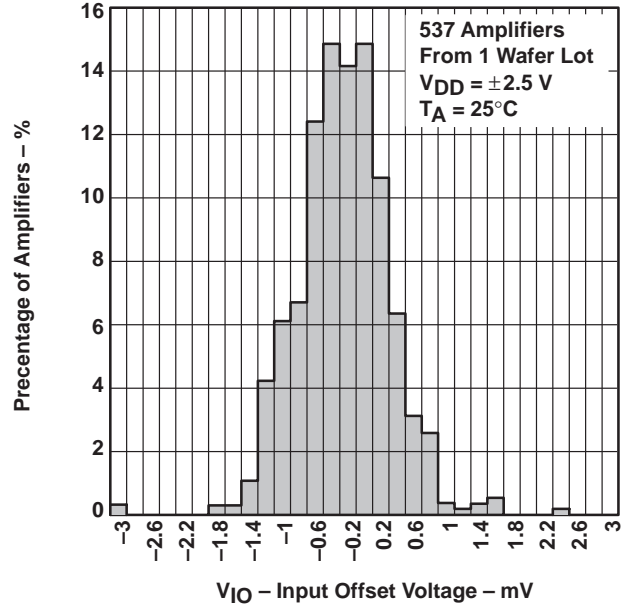


Figure 2

**INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE**

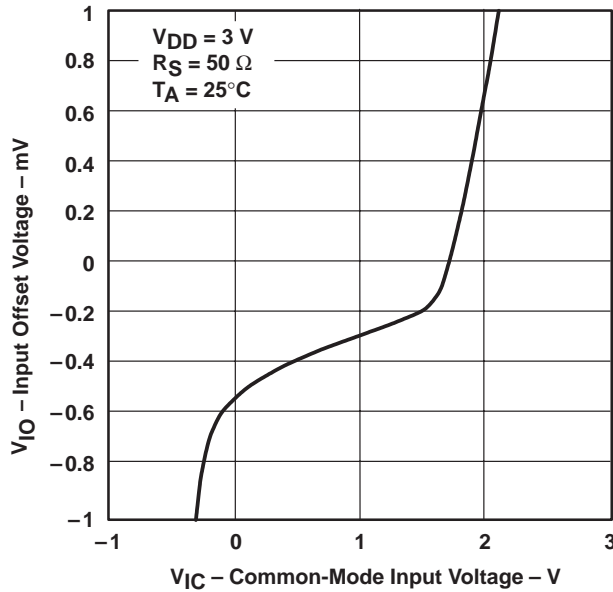


Figure 3

**INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE**

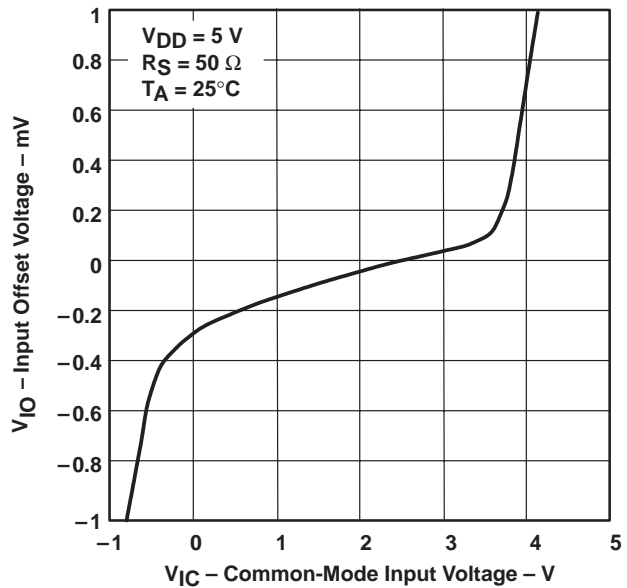


Figure 4

† For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

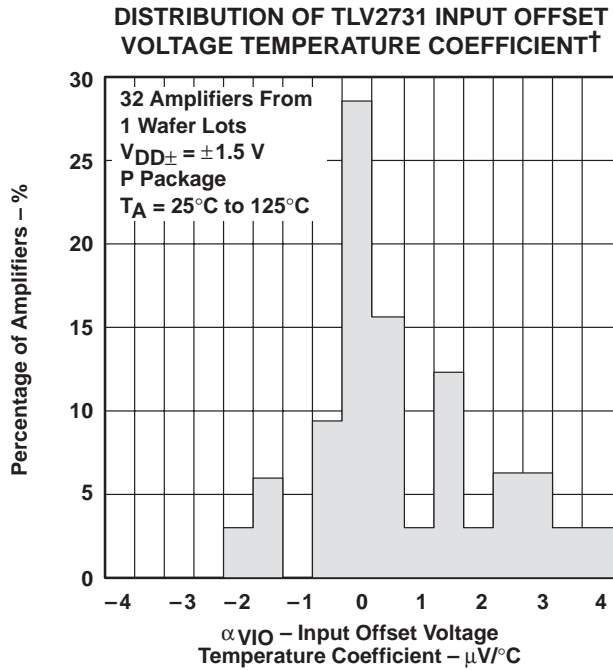


Figure 5

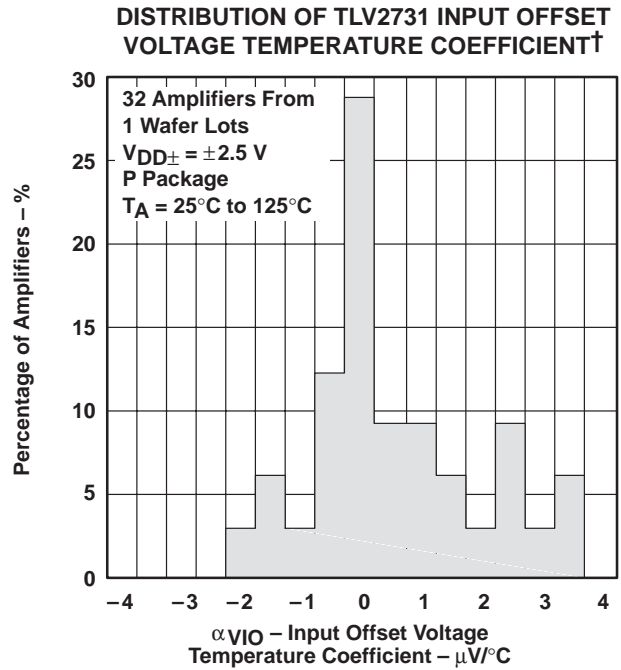


Figure 6

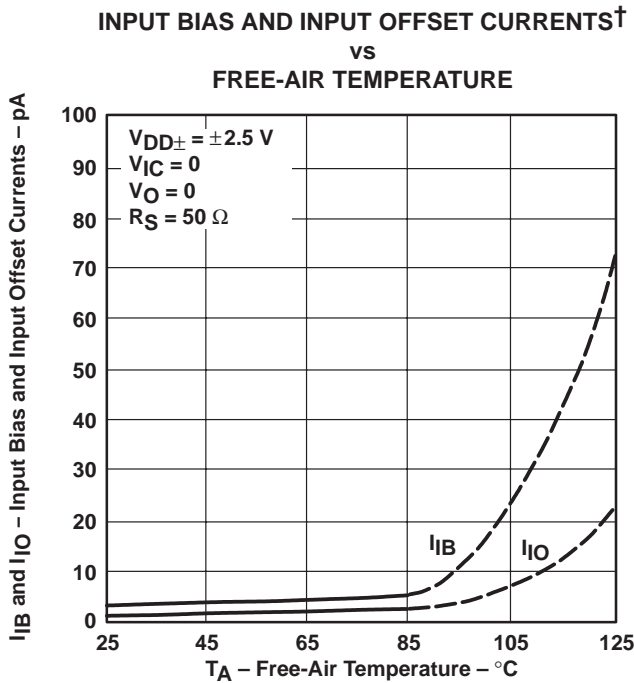


Figure 7

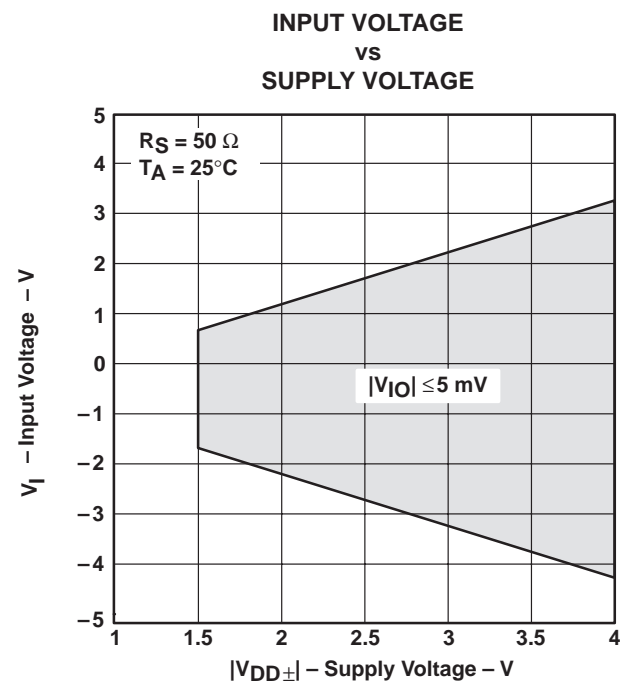


Figure 8

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

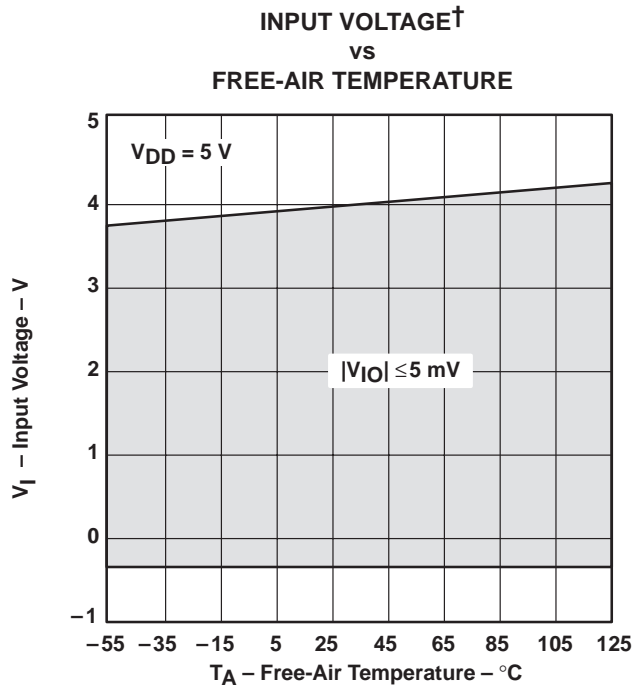


Figure 9

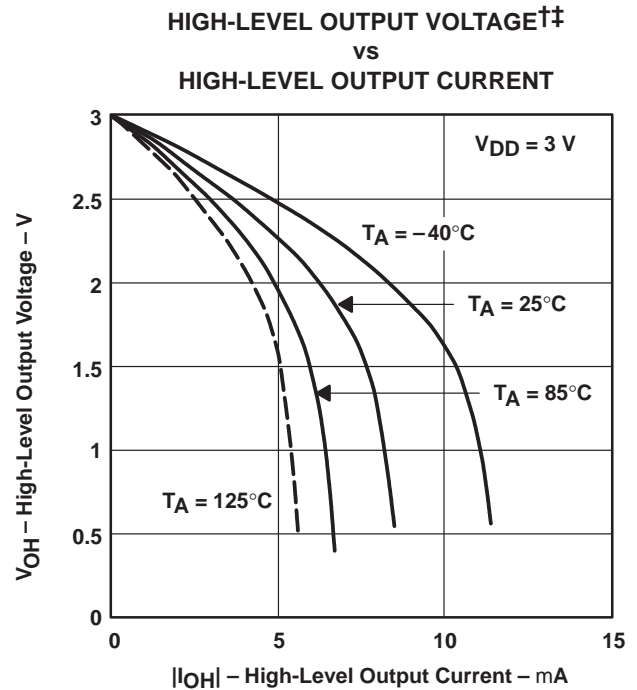


Figure 10

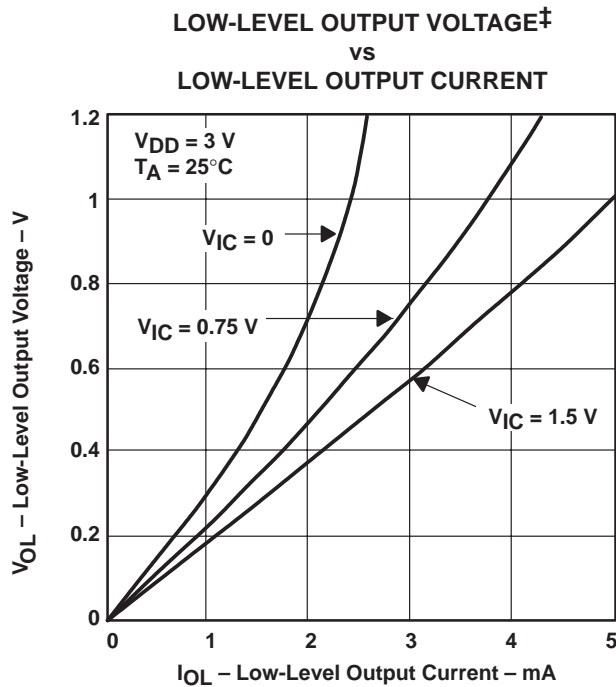


Figure 11

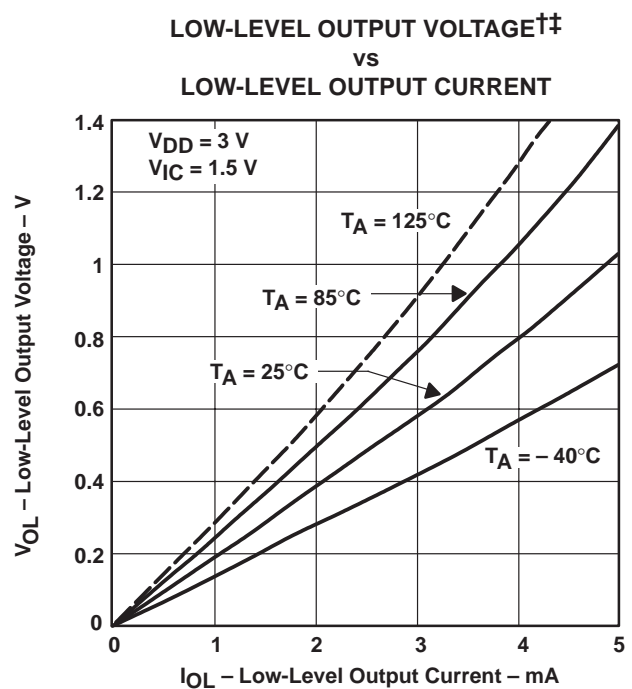


Figure 12

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

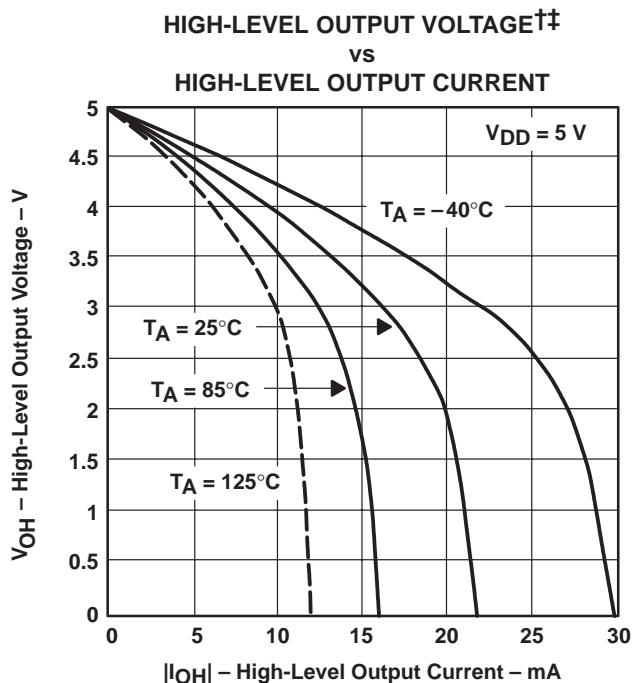


Figure 13

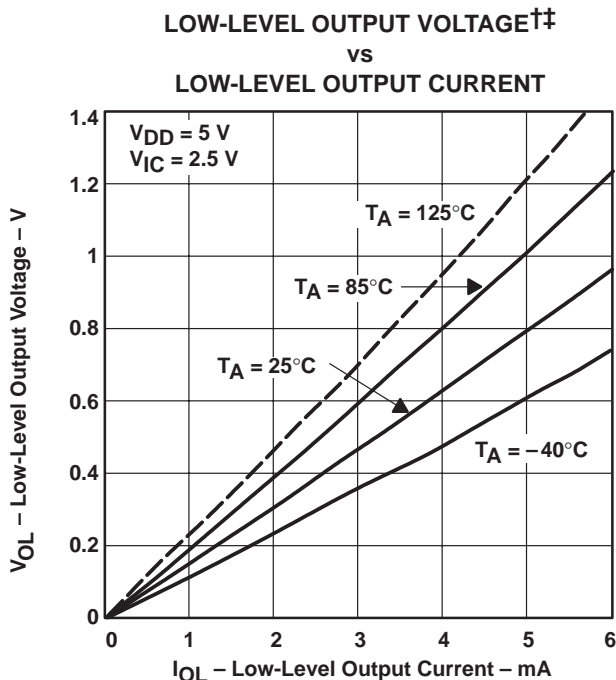


Figure 14

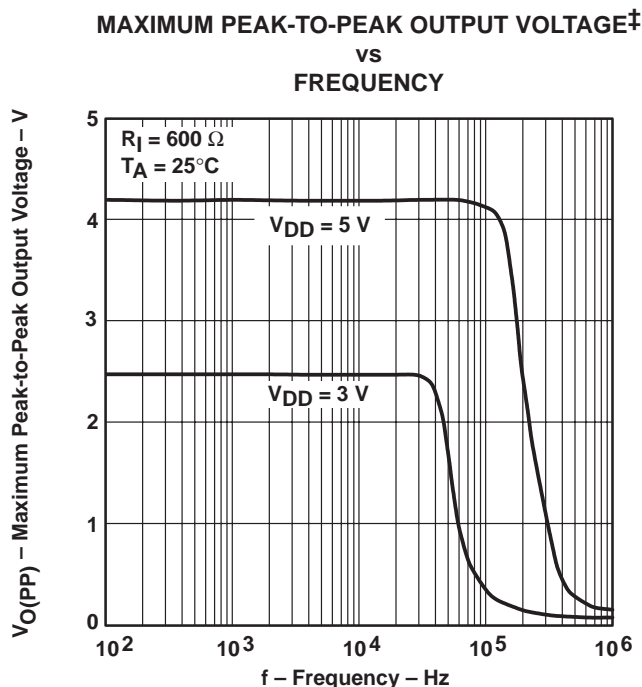


Figure 15

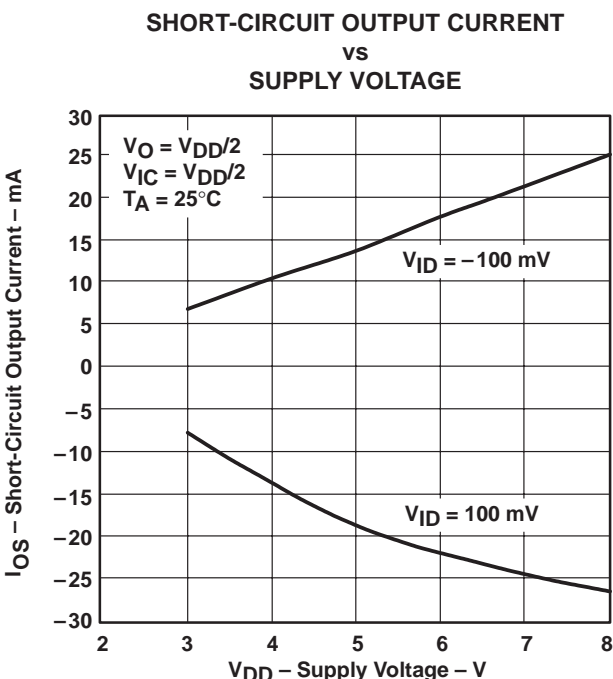


Figure 16

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
 ‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

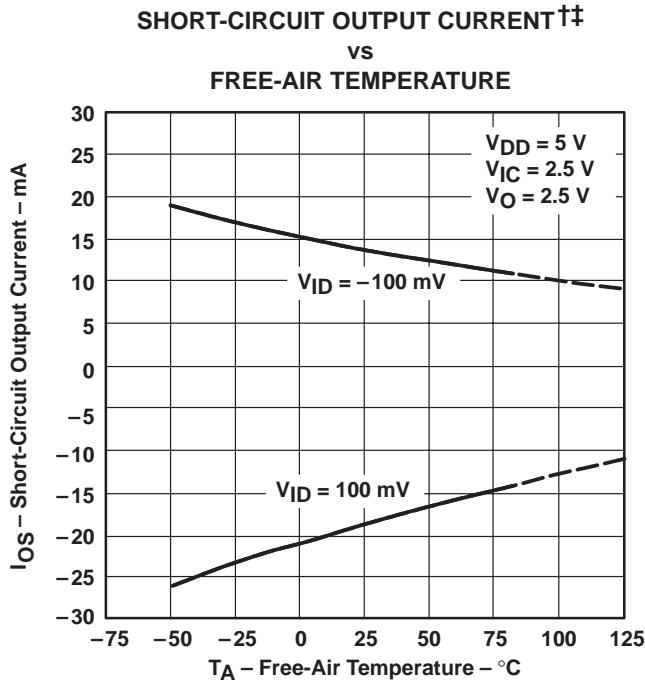


Figure 17

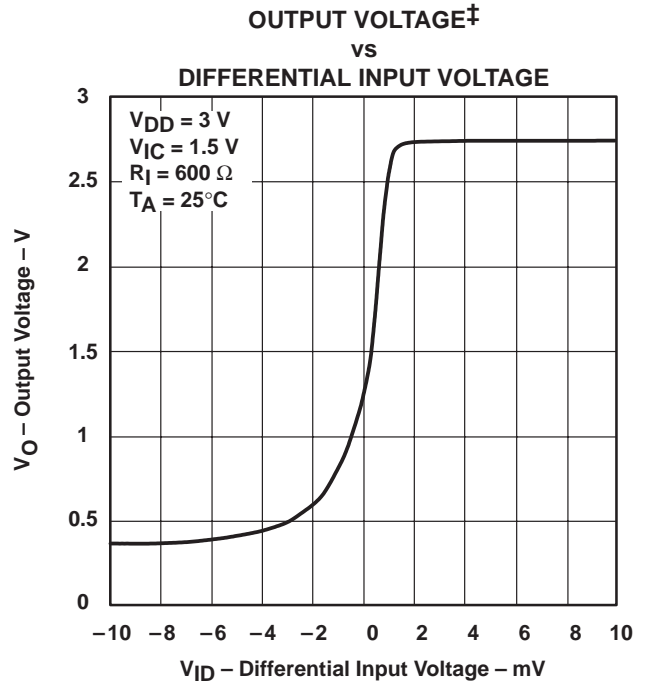


Figure 18

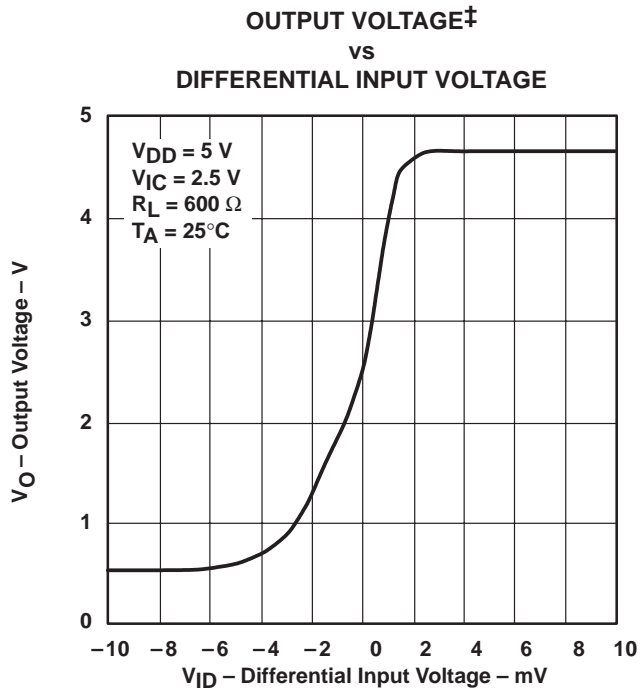


Figure 19

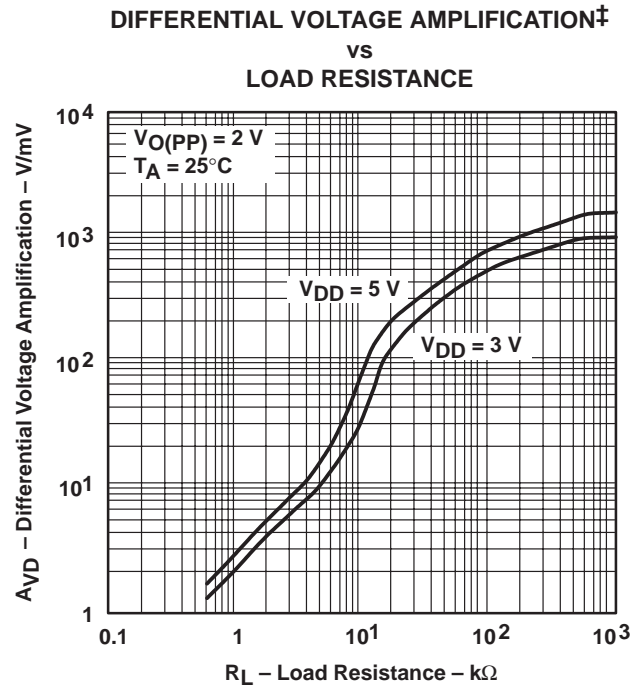


Figure 20

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
 †† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE
 AMPLIFICATION AND PHASE MARGIN†

vs
 FREQUENCY

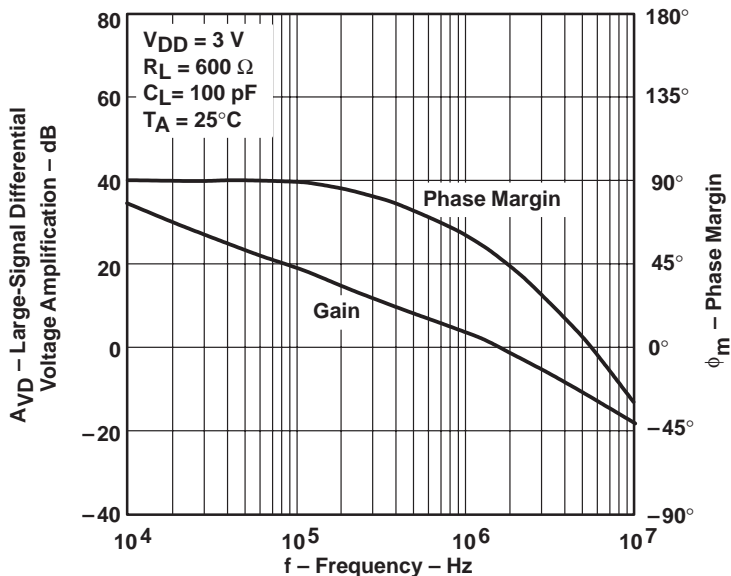


Figure 21

LARGE-SIGNAL DIFFERENTIAL VOLTAGE
 AMPLIFICATION AND PHASE MARGIN†

vs
 FREQUENCY

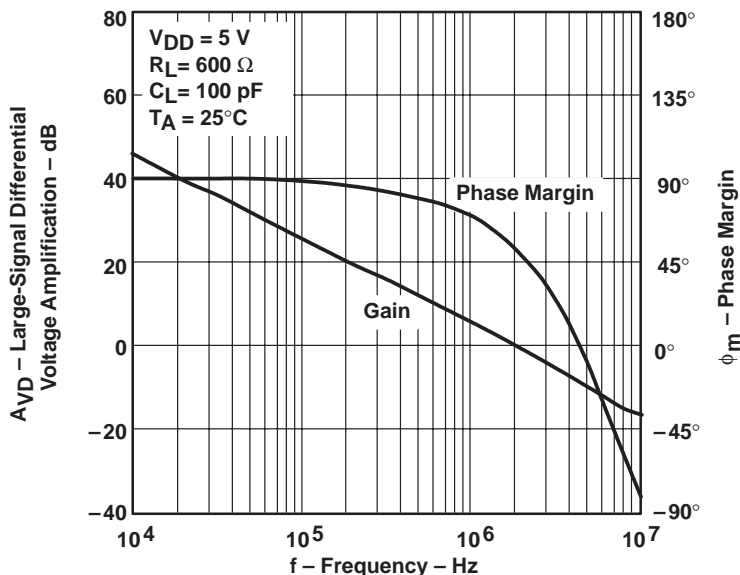


Figure 22

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

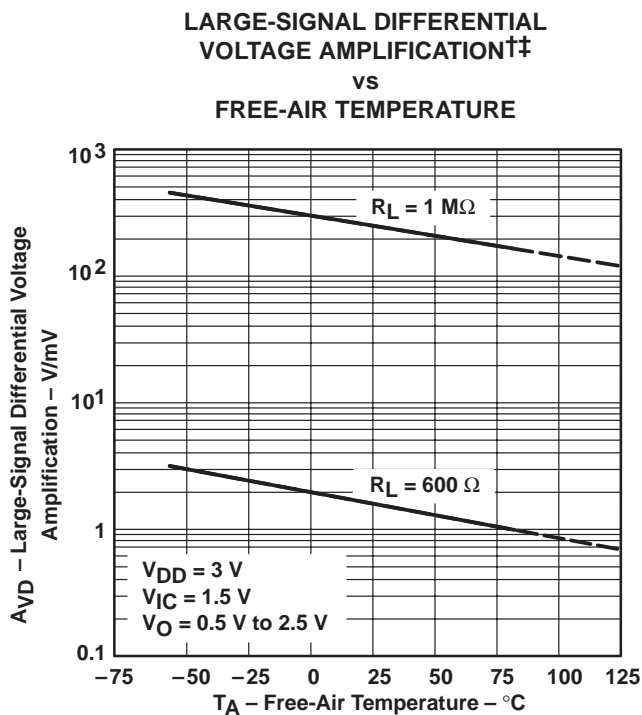


Figure 23

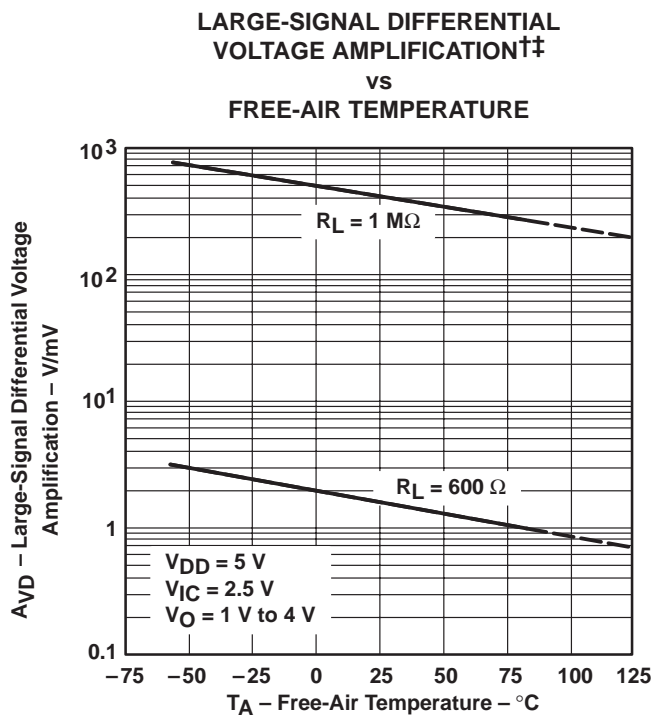


Figure 24

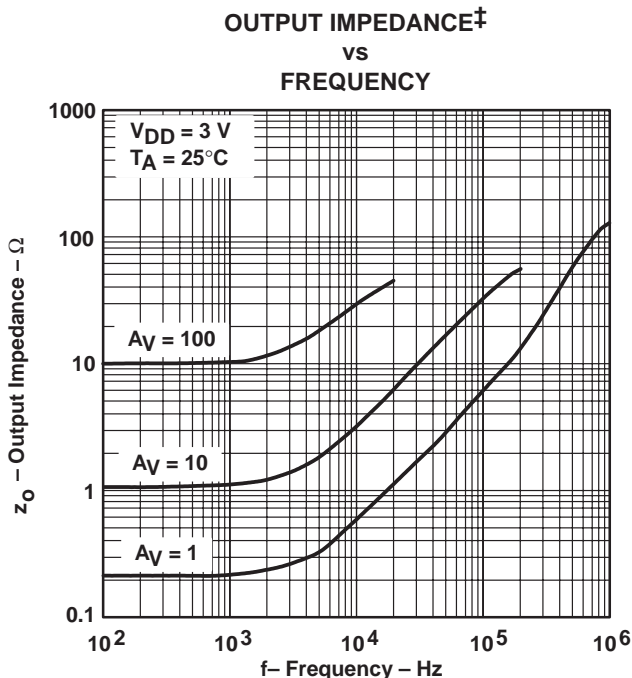


Figure 25

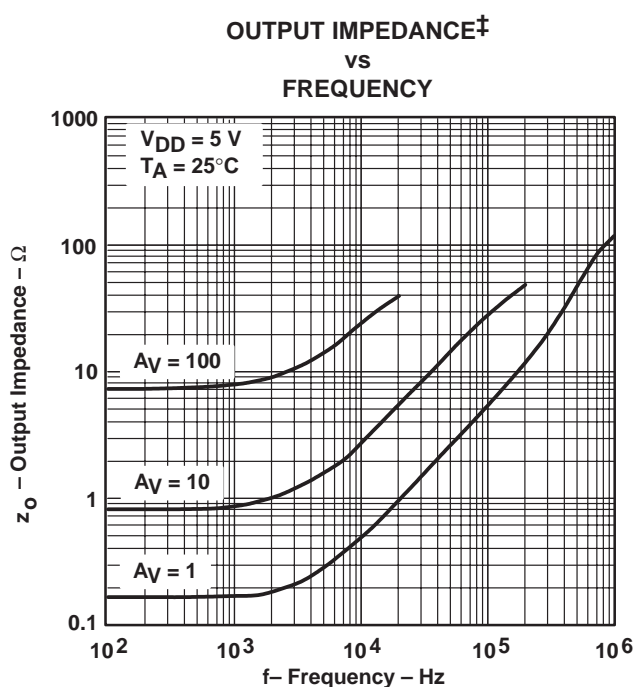


Figure 26

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
 ‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

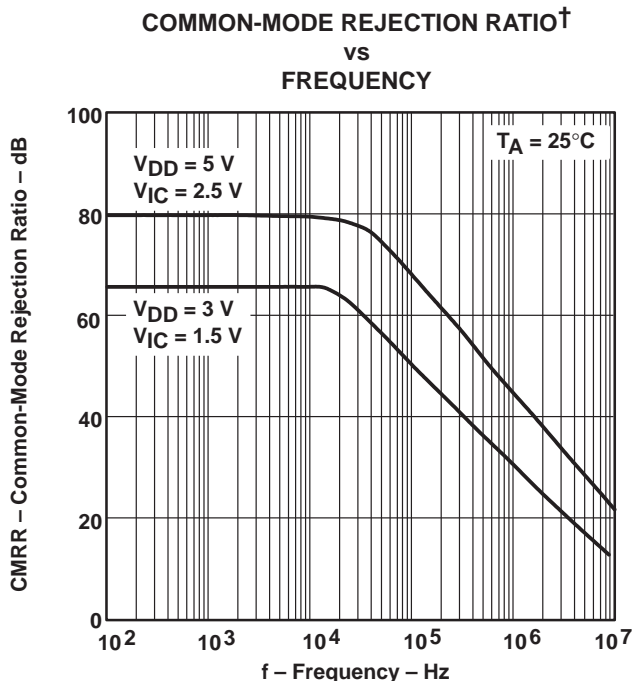


Figure 27

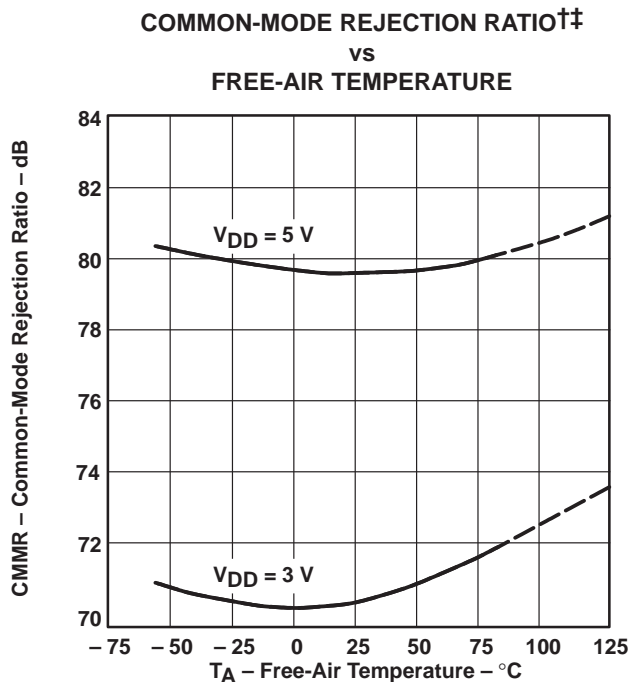


Figure 28

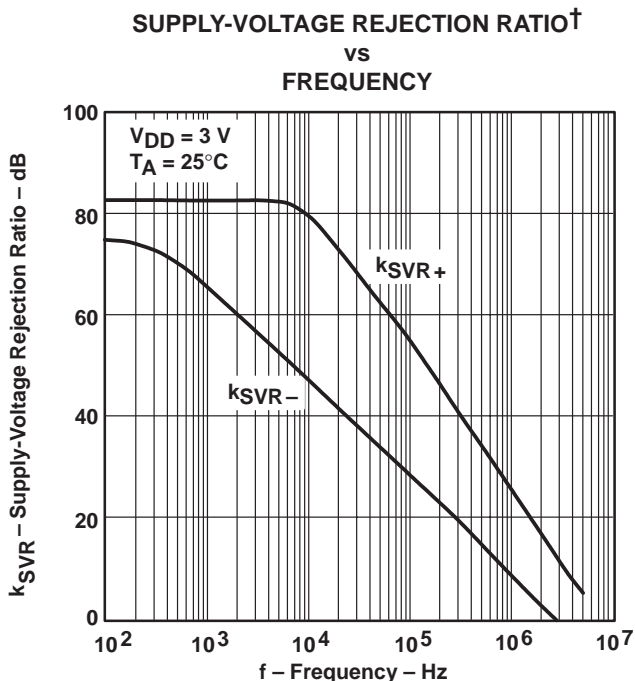


Figure 29

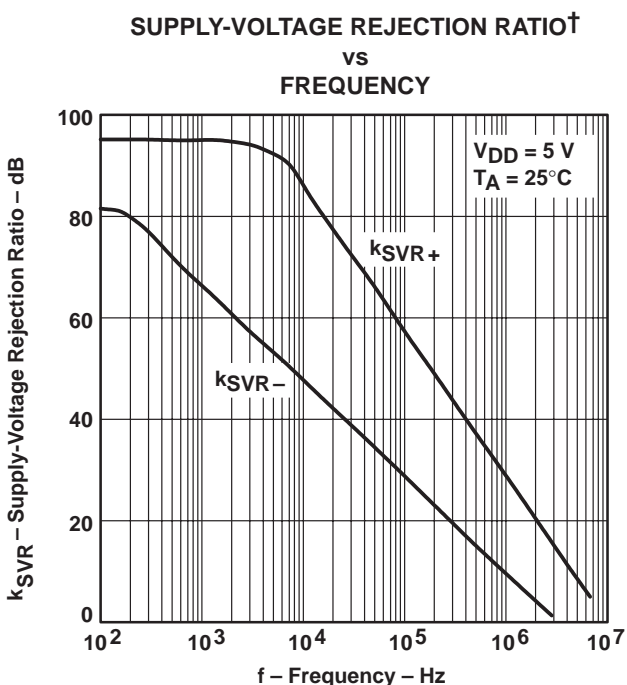
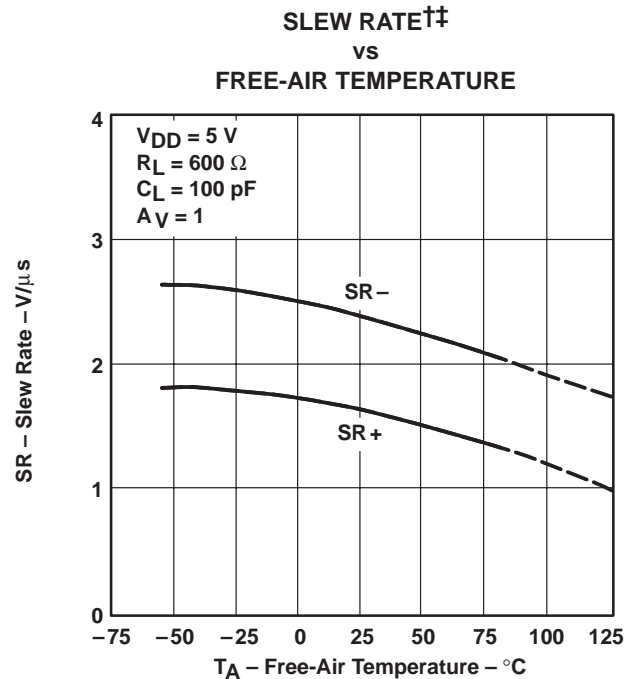
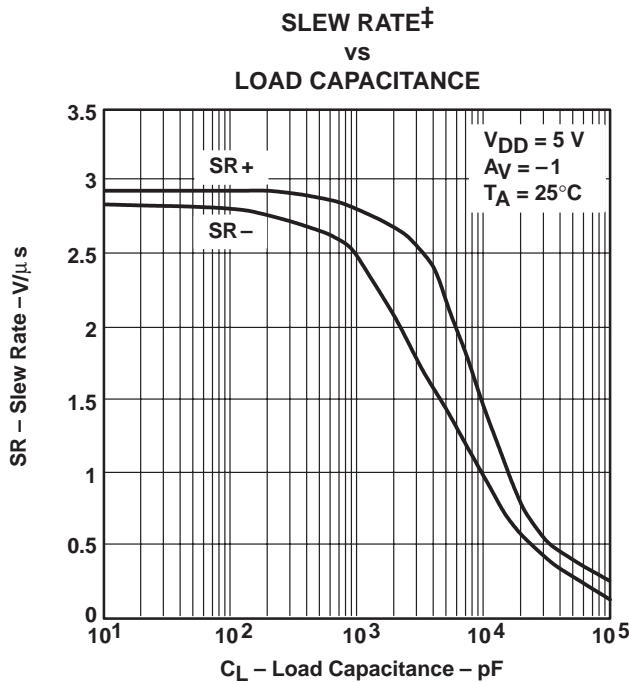
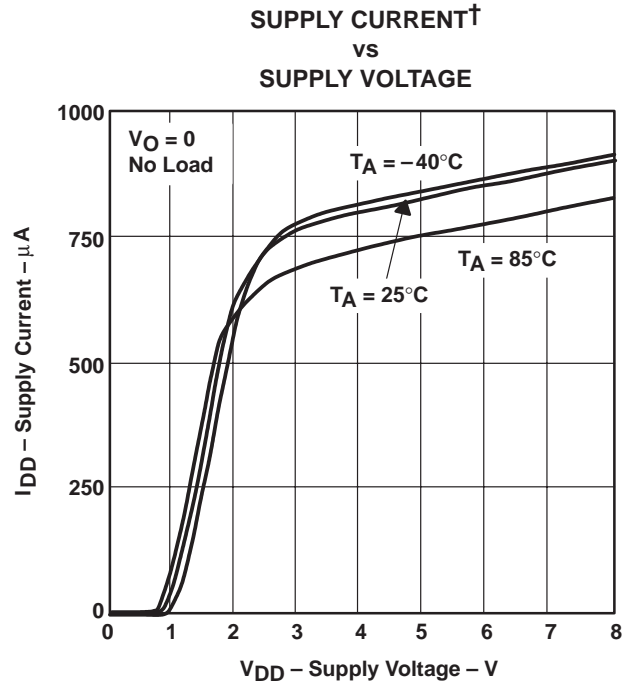
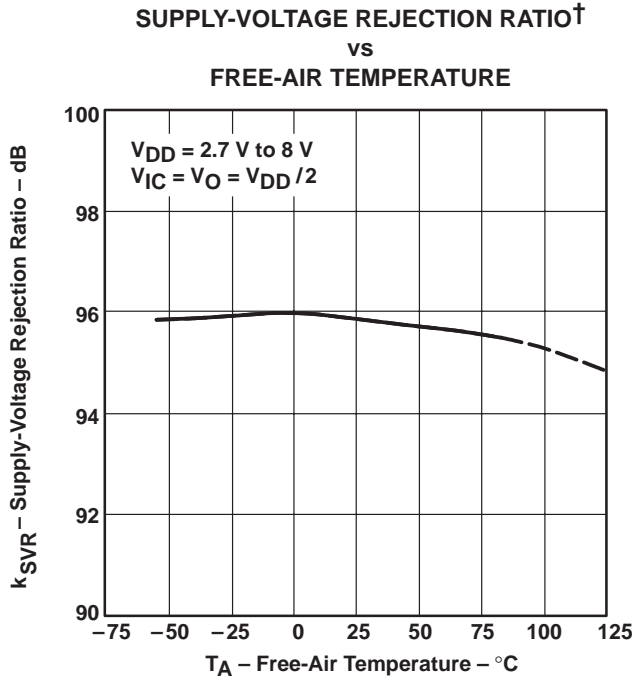


Figure 30

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.
 ‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

INVERTING LARGE-SIGNAL PULSE RESPONSE†

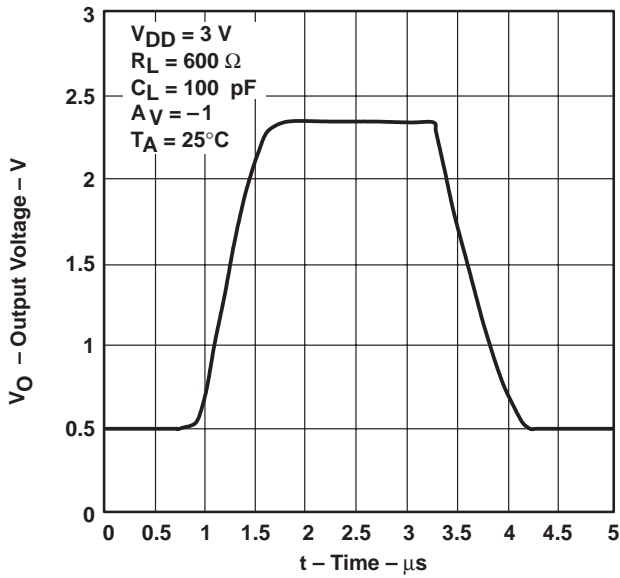


Figure 35

INVERTING LARGE-SIGNAL PULSE RESPONSE†

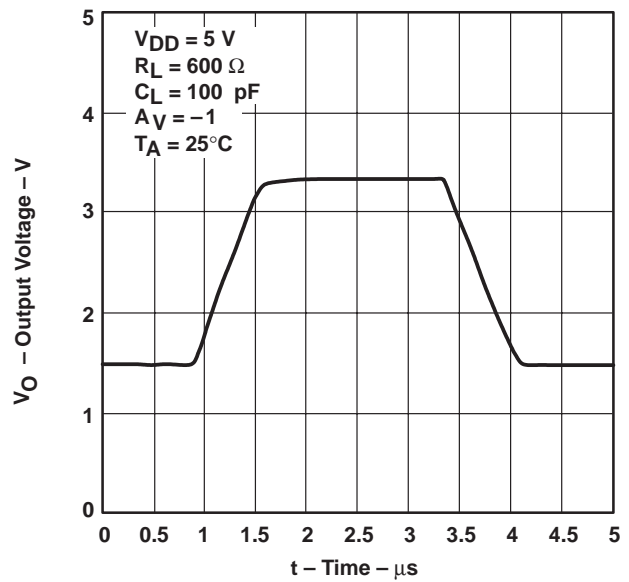


Figure 36

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

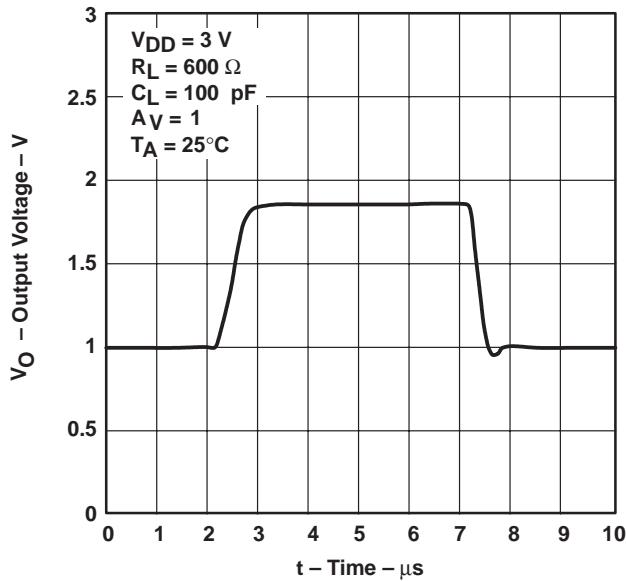


Figure 37

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

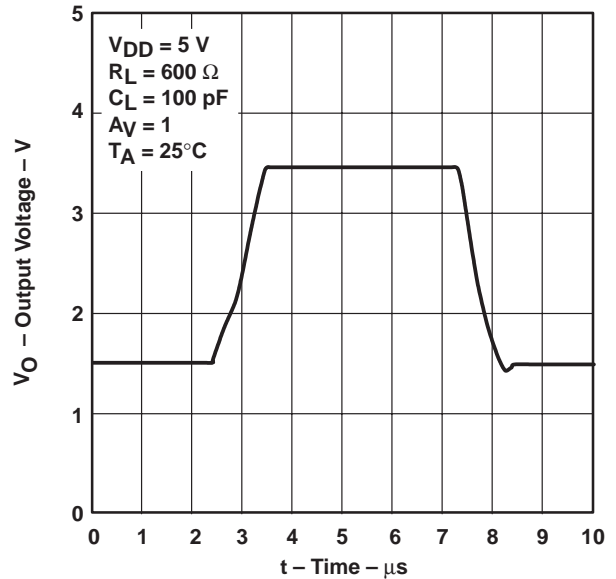


Figure 38

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

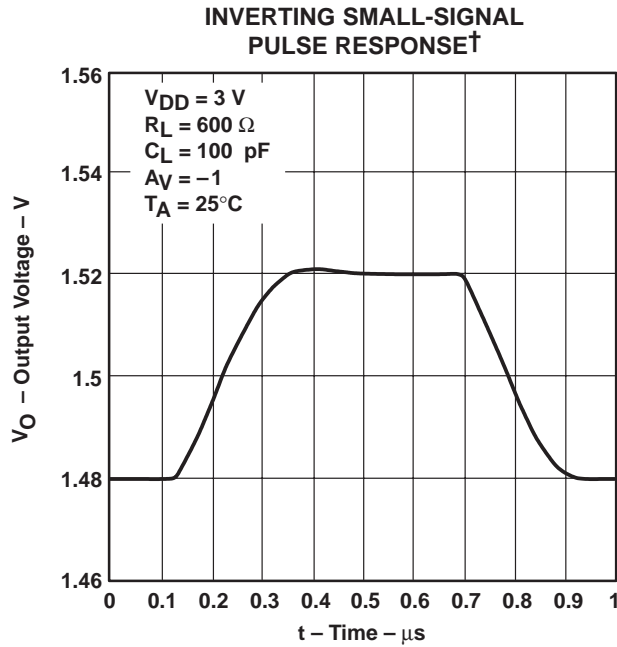


Figure 39

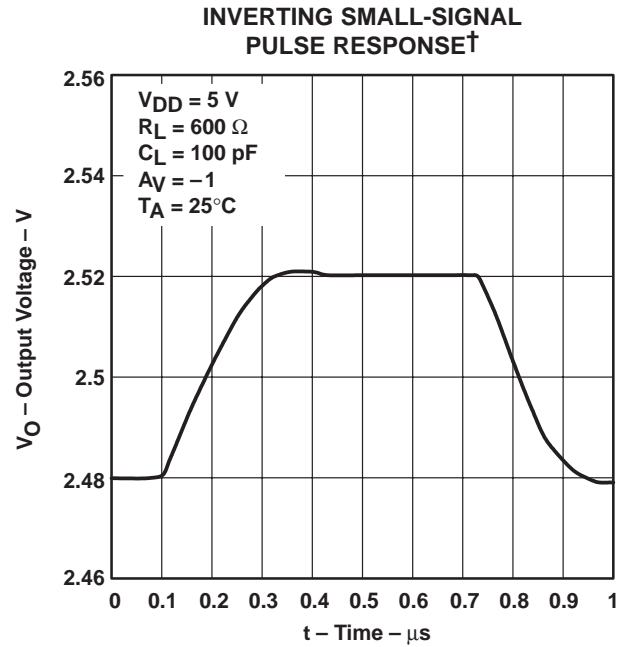


Figure 40

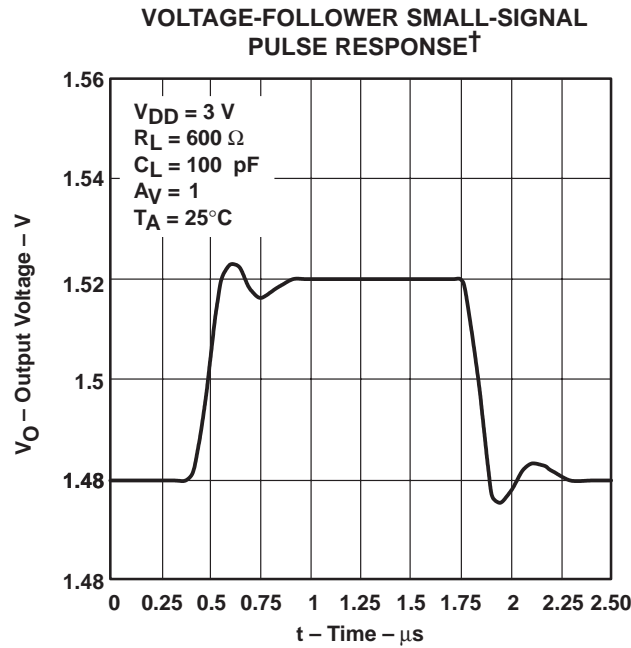


Figure 41

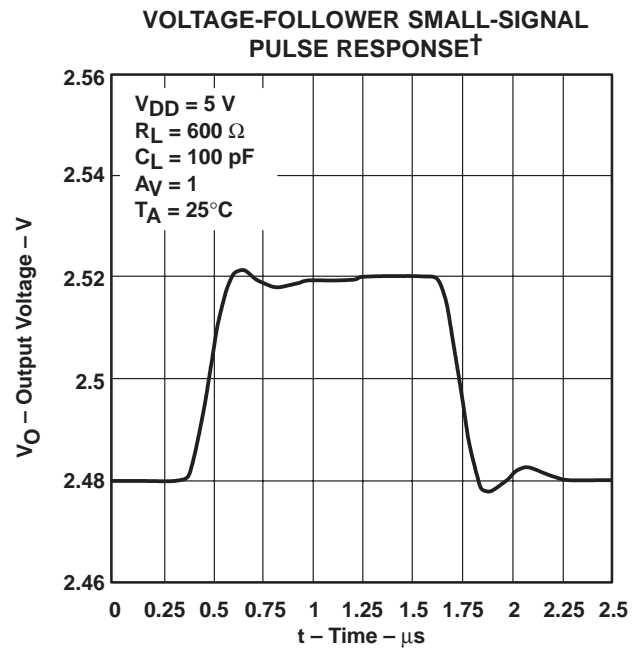


Figure 42

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

EQUIVALENT INPUT NOISE VOLTAGE†
 vs
 FREQUENCY

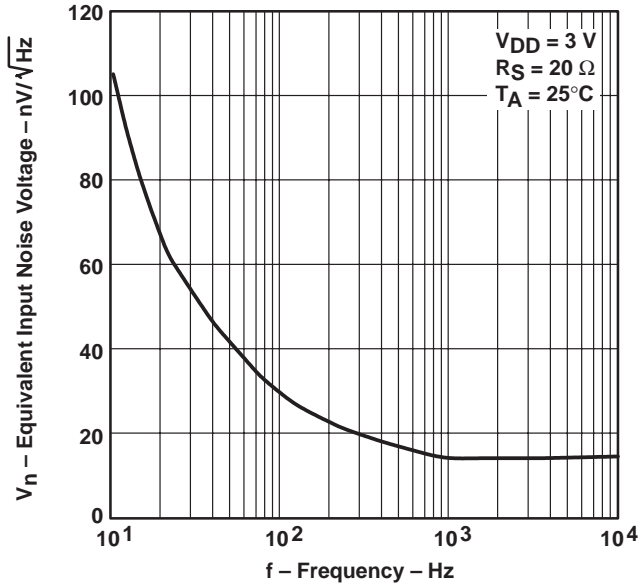


Figure 43

EQUIVALENT INPUT NOISE VOLTAGE†
 vs
 FREQUENCY

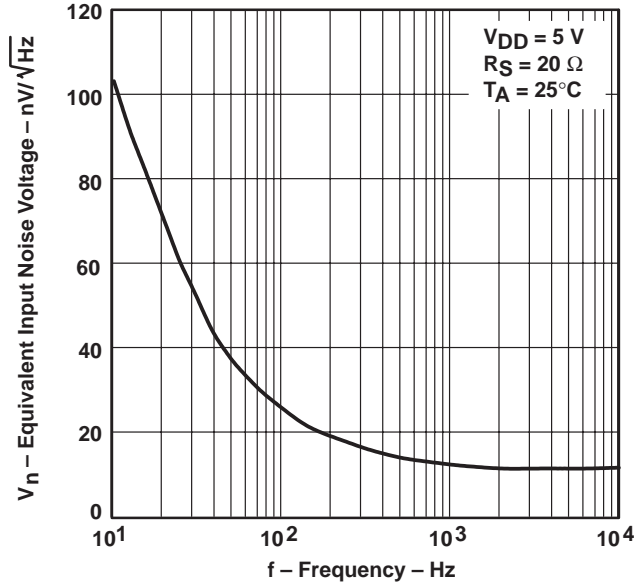


Figure 44

INPUT NOISE VOLTAGE OVER
 A 10-SECOND PERIOD†

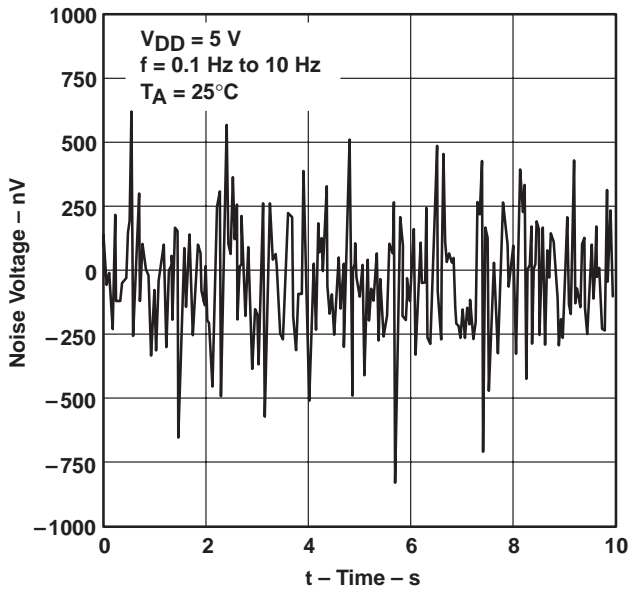


Figure 45

TOTAL HARMONIC DISTORTION PLUS NOISE†
 vs
 FREQUENCY

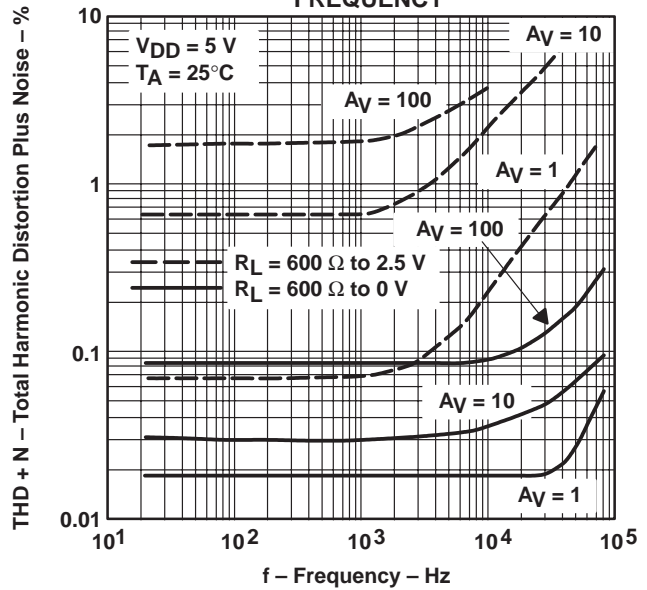
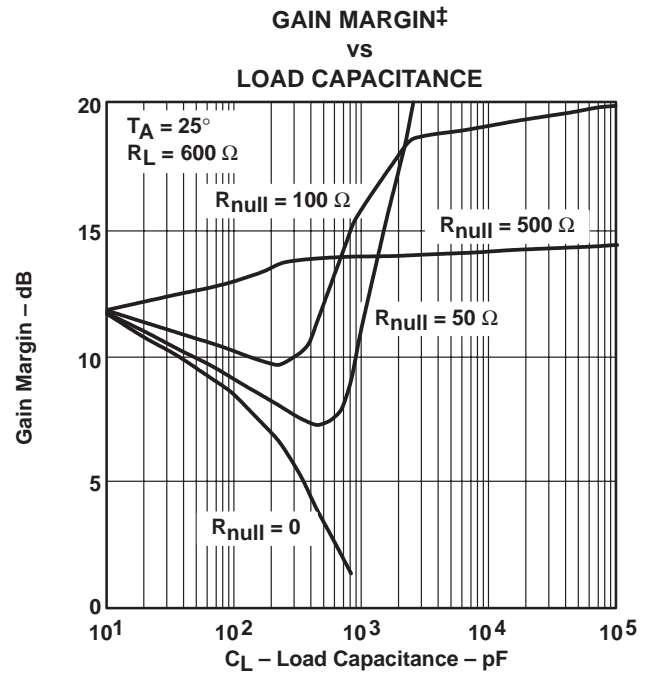
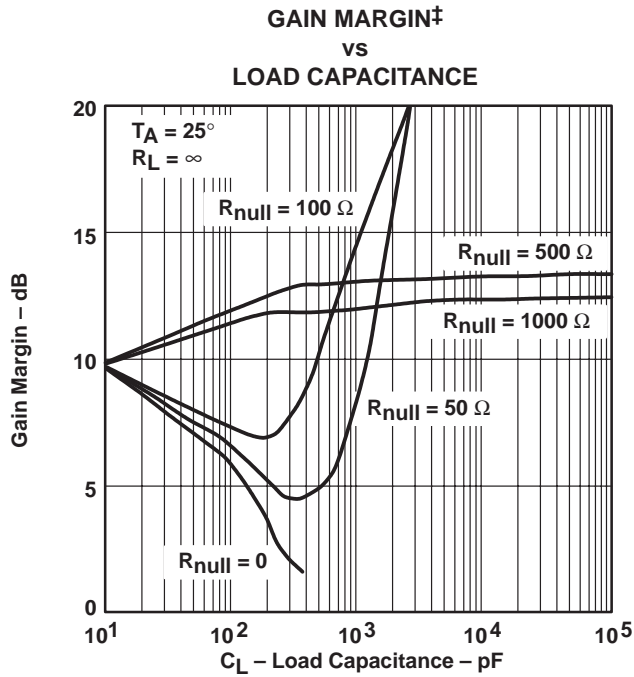
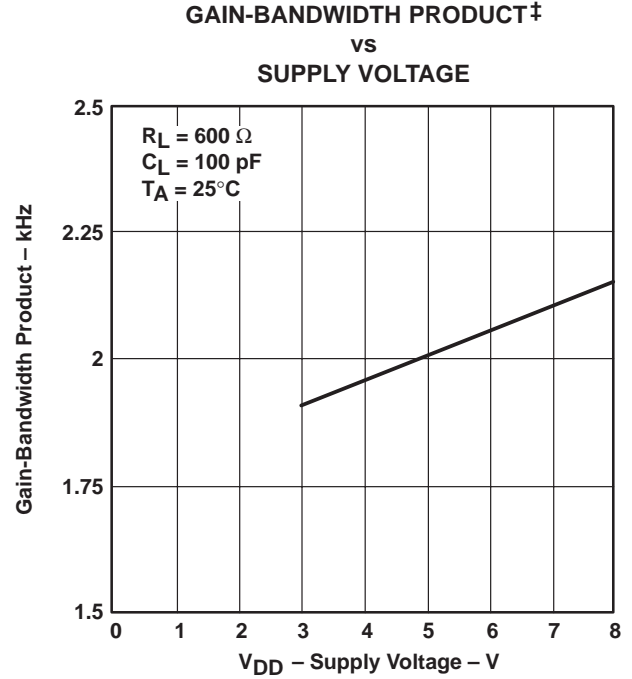
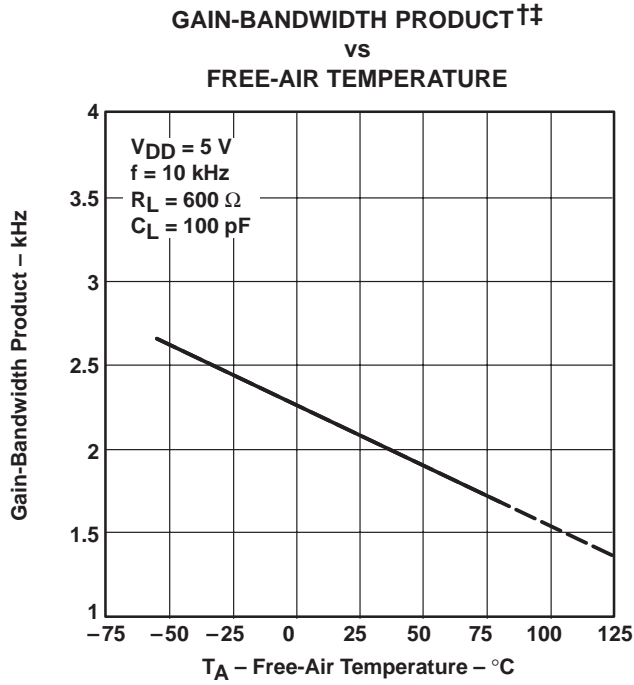


Figure 46

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

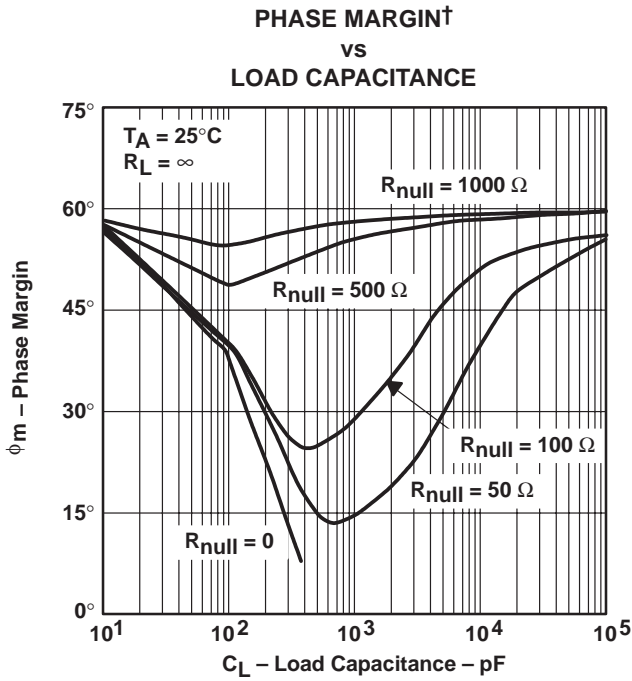


Figure 51

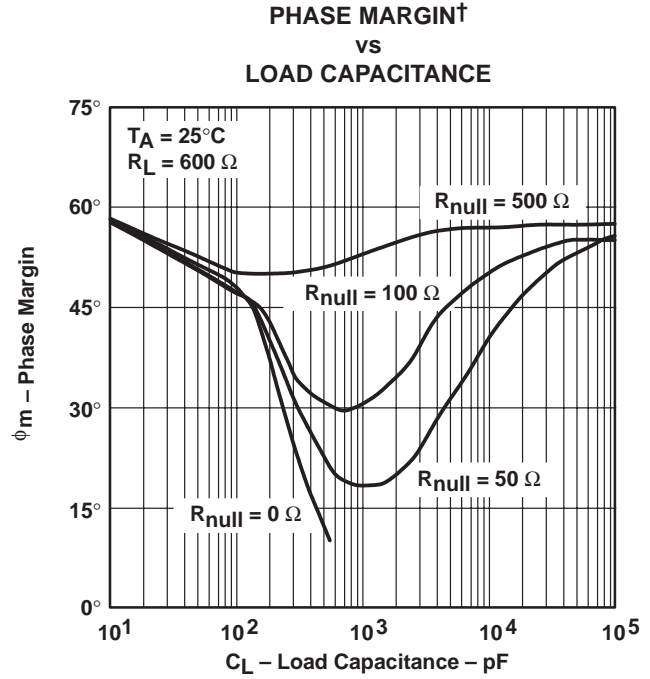


Figure 52

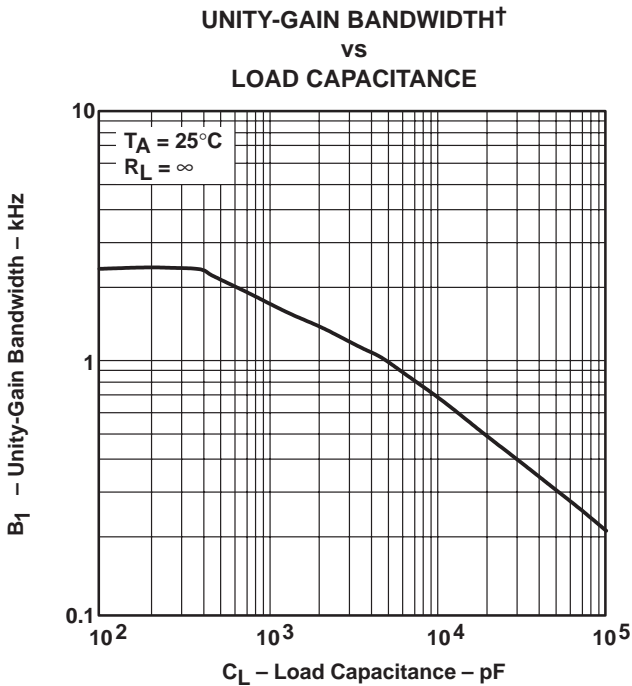


Figure 53

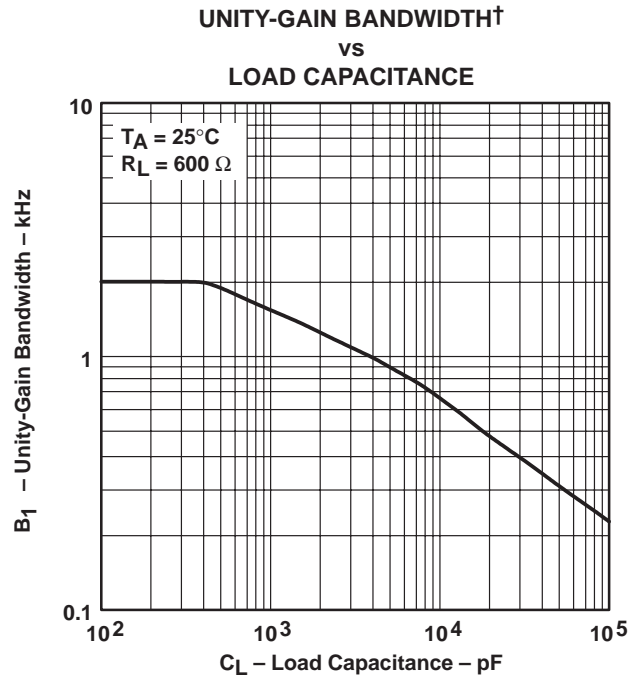


Figure 54

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

APPLICATION INFORMATION

driving large capacitive loads

The TLV2731 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 through Figure 55 illustrate its ability to drive loads greater than 100 pF while maintaining good gain and phase margins ($R_{null} = 0$).

A small series resistor (R_{null}) at the output of the device (see Figure 55) improves the gain and phase margins when driving large capacitive loads. Figure 50 through Figure 53 show the effects of adding series resistances of 50 Ω , 100 Ω , 500 Ω , and 1000 Ω . The addition of this series resistor has two effects: the first effect is that it adds a zero to the transfer function and the second effect is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the approximate improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1} \left(2 \times \pi \times \text{UGBW} \times R_{null} \times C_L \right) \quad (1)$$

where :

- $\Delta\phi_{m1}$ = improvement in phase margin
- UGBW = unity-gain bandwidth frequency
- R_{null} = output series resistance
- C_L = load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 54 and Figure 55). To use equation 1, UGBW must be approximated from Figure 54 and Figure 55.

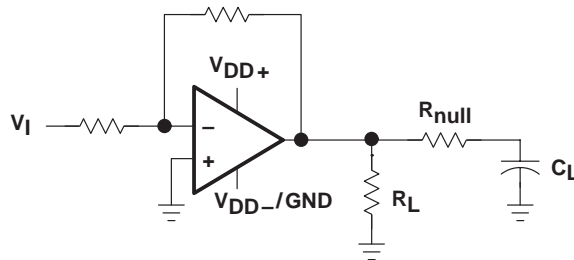


Figure 55. Series-Resistance Circuit

APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 6) and subcircuit in Figure 57 are generated using the TLV2731 typical electrical and operating characteristics at T_A = 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

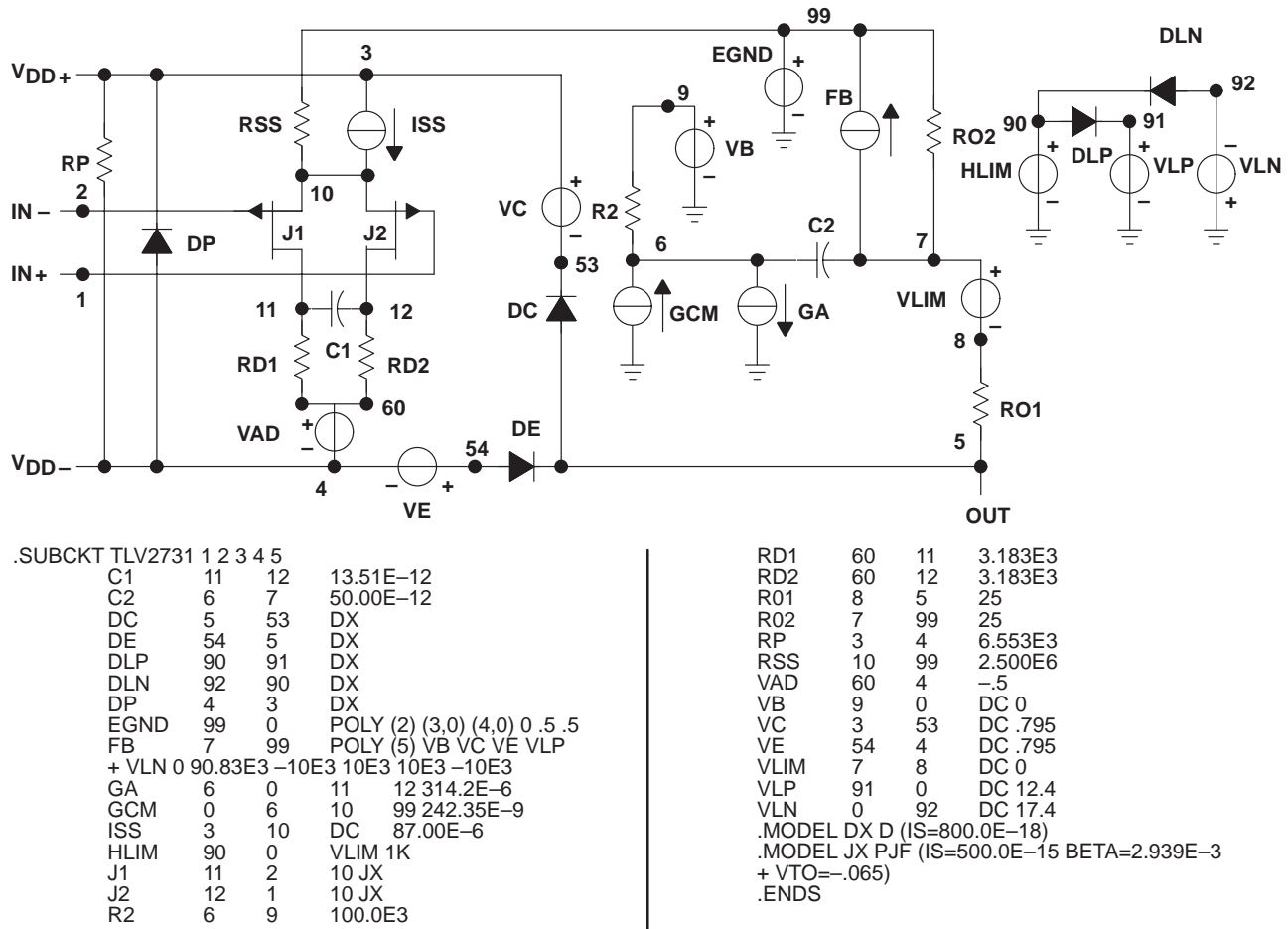


Figure 56. Boyle Macromodel and Subcircuit

PSpice and Parts are trademark of MicroSim Corporation.

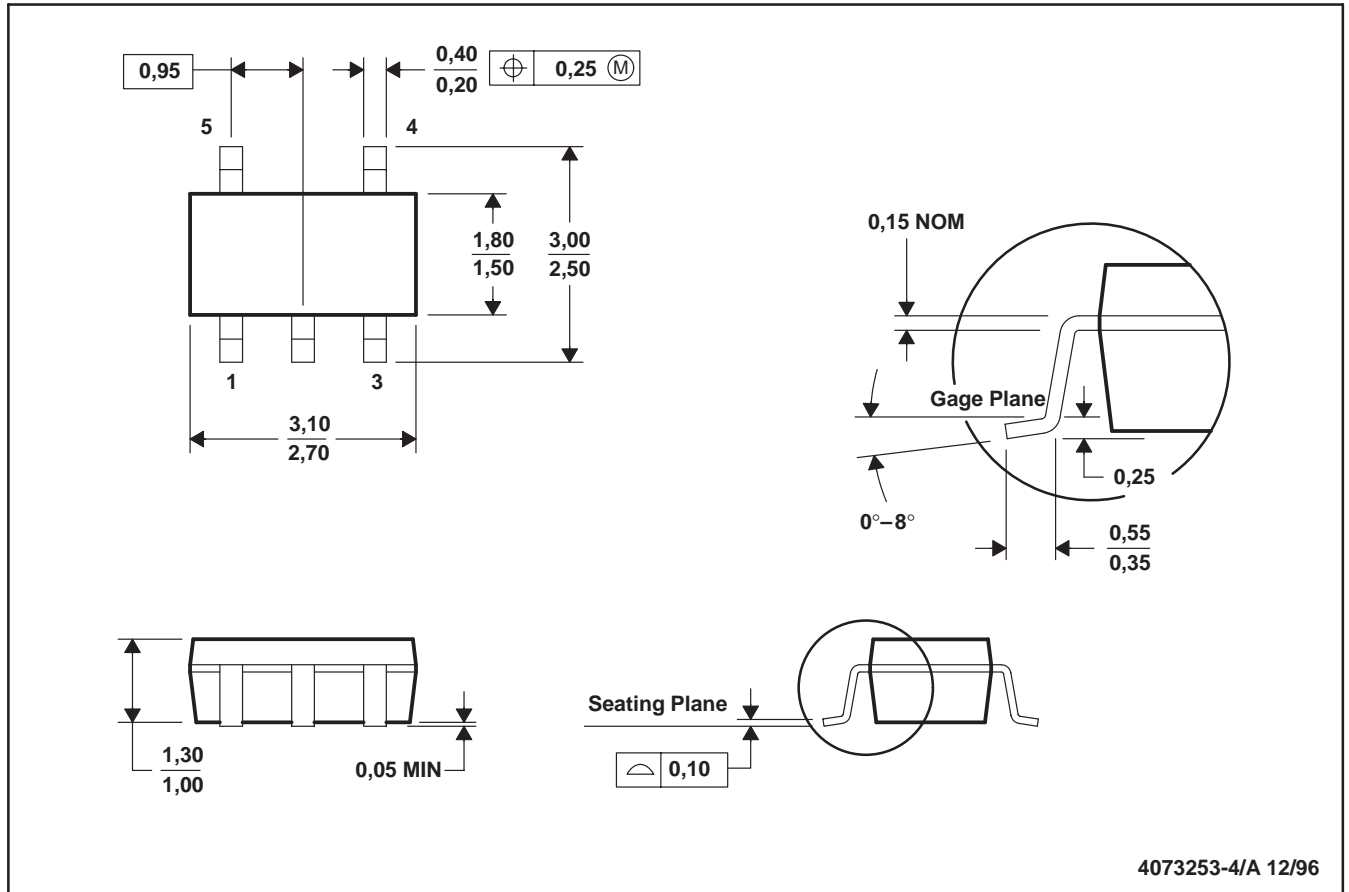
Macromodels, simulation models, or other models provided by TI, directly or indirectly, are not warranted by TI as fully representing all of the specification and operating characteristics of the semiconductor product to which the model relates.



MECHANICAL INFORMATION

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions include mold flash or protrusion.

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.